

EPIGAP Optronik GmbH

Koepenicker Str. 325b, Haus 41
 D-12555 Berlin
 Fon: +49 (0)30 657637 60
 Fax: +49 (0)30 657637 70
 sales@epigap-optronic.de



Product Data Sheet

Preliminary

LED Chip UV

EOLC-365-34

Rev. 01 aus 2011

Radiation	Type	Electrodes
Ultra violet		P + N up

	<p>Description</p> <ul style="list-style-type: none"> -Substrate: Sapphire, epitaxial layer: GaN based Material -N bonding pad electrode: Au alloy -P bonding pad electrode: Au alloy -Emission area: 201 μm x 201 μm -Bottom area: 280 μm x 280 μm ± 20 μm -Chip thickness: 120 μm ± 10 μm -Bonding pad electrodes: (each) 90 μm -Electrodes spacing: 128 μm
--	---

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =20mA	V _F	3.2	3.6	4.2	V
Reverse current	V _R =5V	I _R			10	μA
Peak wavelength	I _F =20mA	λ _p	363		370	nm
Full width at half maximum	I _F =20mA	Δλ		15		nm
Optical power output	I _F =20mA	P _o	1.0		1.5	mW

Spectrum

